

an AND function circuit. However, the pair of transistors M3, M5 and M4, M6 are the OR function circuit. Therefore, the pair of transistors, M3, M5 and M4, M6 can not be replaced with a dual-gated transistor.

It is anticipated that the Examiner is associating the Applicant's claimed "dual-gated" transistor with a conventional dual gate MESFET as used in microwave devices and which performs an AND function circuit. This association is not intended. A dual gate MESFET, as the same is conventionally known, includes a pair of gates located only on one side of a single body region of a transistor. This then results in the AND circuit function.

In contrast, and as illustrated in the Applicant's drawings, the present invention refers to "dual-gated" transistors in which gates are located on opposing sides of a single body region of a transistor. Such a configuration is also referred to as a dual-gate or double-gated structure in silicon technology. However, in this configuration the arrangement can perform an OR function circuit as used in the present case. That is, a channel can independently be formed on each side of the single body region and still produce conductivity through the transistor. This is the structure illustrated in connection with Figures 2A and 3. The single box-like structure illustrates a single body region which has gates on opposing sides of the single body region. The description provided in the Applicant's specification on page 10 accords with this characterization. Applicant's "dual-gated" transistor is to be distinguished from both a convention dual gate MESFET as well as from a number of transistors coupled simple in parallel fashion. The Applicant's "dual-gated" transistor structure can be further understood by reference to US patent number 6,104,068 which shares a common inventor to the present case. Thus, Applicant believes that the pair of "dual-gated" transistors, the first being M3, M5 and the second being M4, M6, are properly described in the specification. Accordingly, withdrawal of the objection to the specification is respectfully solicited.

REMARKS

Applicant has carefully reviewed and considered the Office Action mailed on November 8, 2000, and the references cited therewith.

No amendment is made to the claims. Claims 1-45 are pending in this application.